



DMG3414U

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

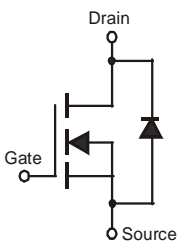
- Low On-Resistance
 - 25mΩ @ $V_{GS} = 4.5V$
 - 29mΩ @ $V_{GS} = 2.5V$
 - 37mΩ @ $V_{GS} = 1.8V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

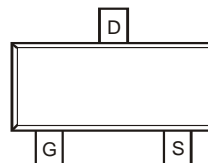
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)



TOP VIEW



Internal Schematic



TOP VIEW

Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25^\circ C$	I_D	4.2	A
		$T_A = 70^\circ C$		3.2	
Pulsed Drain Current (Note 4)			I_{DM}	30	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_D	0.78	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ C$	$R_{\theta JA}$	162	$^\circ C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

- Notes:
1. No purposefully added lead.
 2. Device mounted on FR-4 PCB with 2oz. Copper and test pulse width $t \leq 10s$.
 3. Repetitive rating, pulse width limited by junction temperature.

NEW PRODUCT

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	T _J = 25°C V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	0.5	—	0.9	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	19	25	mΩ	V _{GS} = 4.5V, I _D = 8.2A
			22	29		
			28	37		
Forward Transfer Admittance	Y _{fs}	—	7	—	S	V _{DS} = 10V, I _D = 4A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	829.9	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	85.3	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	81.2	—	pF	
Total Gate Charge	Q _g	—	9.6	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 8.2A
Gate-Source Charge	Q _{gs}	—	1.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	3.5	—	nC	
Turn-On Delay Time	t _{D(on)}	—	8.1	—	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 10Ω, R _G = 6Ω, I _D = 1A
Turn-On Rise Time	t _r	—	8.3	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	40.1	—	ns	
Turn-Off Fall Time	t _f	—	9.6	—	ns	

Notes: 4. Short duration pulse test used to minimize self-heating effect.